

N-channel 20 V, 0.030 Ω typ, 5 A STripFET™ II Power MOSFET in a SO-8 package

Datasheet - production data

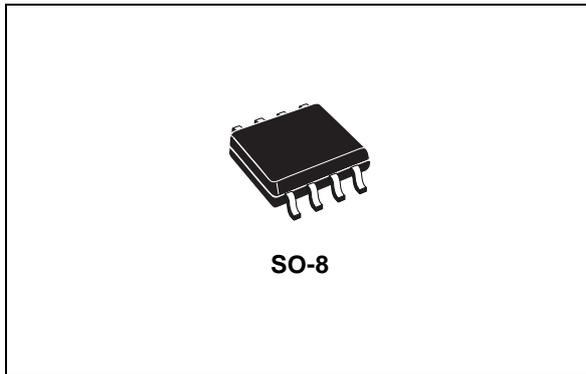
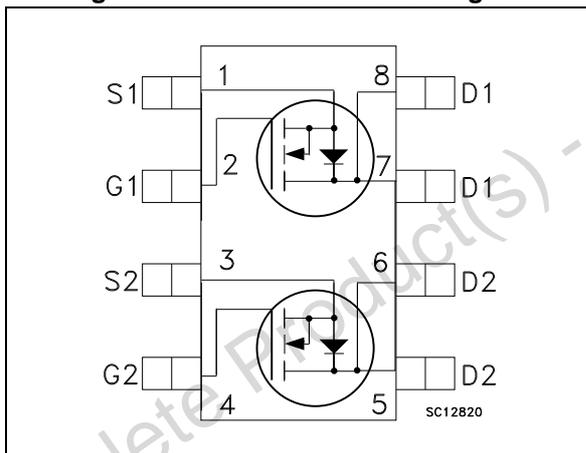


Figure 1. Internal schematic diagram



Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STS5DNF20V	20 V	0.040 Ω @ 4.5 V	5 A
		0.045 Ω @ 2.7 V	

- Ultra low threshold gate drive (2.7 V)
- Standard outline for easy automated surface mount assembly

Applications

- Switching application

Description

This Power MOSFET has been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

Table 1. Device summary

Order code	Marking	Package	Packaging
STS5DNF20V	5DF20V	SO-8	Tape and reel

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Obsolete Product(s) - Obsolete Product(s)



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	20	V
V_{GS}	Gate-source voltage	± 12	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	20	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ (dual operation)	1.6	W
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ (single operation)	2	W
T_J	Max. operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		

1. Pulse width limited by safe operating area.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal resistance junction-ambient single operation	62.5	$^\circ\text{C}/\text{W}$
	Thermal resistance junction-ambient dual operation	78	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	20			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = 20$			1	μA
		$V_{DS} = 20\ \text{V}$, $T_C = 125\text{ °C}$			10	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 12\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	0.6			Ω
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 4.5\ \text{V}$, $I_D = 2.5\ \text{A}$		0.030	0.040	Ω
		$V_{GS} = 2.7\ \text{V}$, $I_D = 2.5\ \text{A}$		0.037	0.045	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$	-	460		pF
C_{oss}	Output capacitance		-	200		pF
C_{rss}	Reverse transfer capacitance		-	50		pF
Q_g	Total gate charge	$V_{DD} = 16\ \text{V}$, $I_D = 5\ \text{A}$, $V_{GS} = 4.5\ \text{V}$ (see Figure 13)	-	8.5	11.5	nC
Q_{gs}	Gate-source charge		-	1.8		nC
Q_{gd}	Gate-drain charge		-	2.4		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 10\ \text{V}$, $I_D = 2.5\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\ \text{V}$ (see Figure 12)	-	7	-	ns
t_r	Rise time		-	33	-	ns
$t_{d(off)}$	Turn-off delay time		-	27	-	ns
t_f	Fall Time		-	10	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $V_{DD} = 10\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 14)	-	26		ns
Q_{rr}	Reverse recovery charge		-	13		nC
I_{RRM}	Reverse recovery current		-	1		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Obsolete Product(s) - Obsolete Product(s)

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

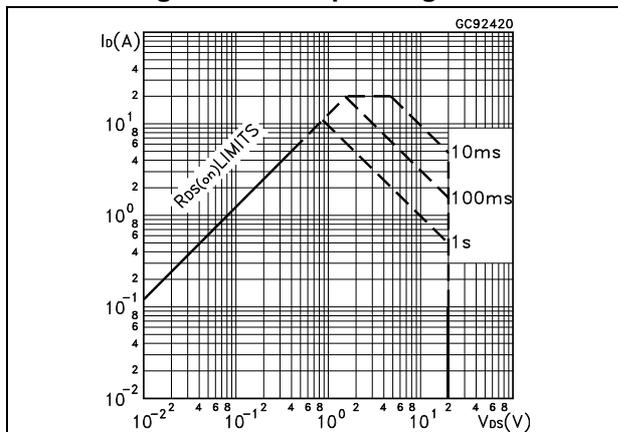


Figure 3. Thermal impedance

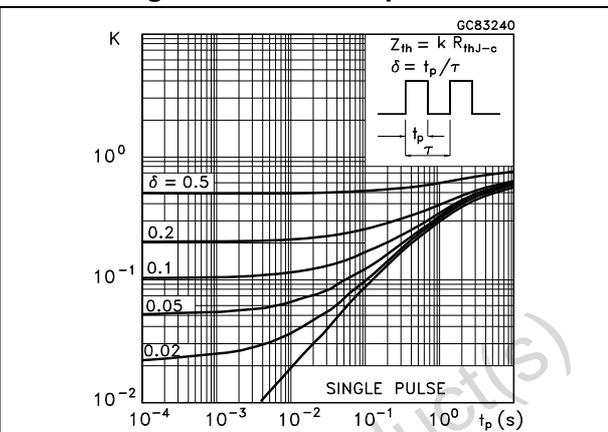


Figure 4. Output characteristics

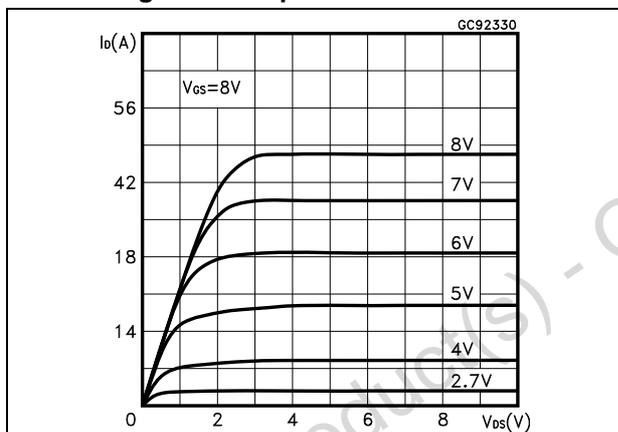


Figure 5. Transfer characteristics

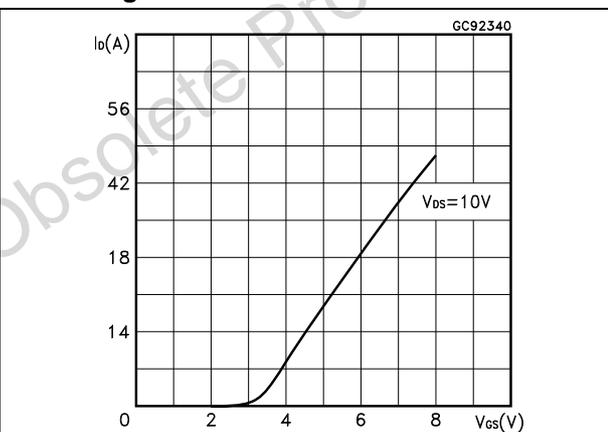


Figure 6. Source-drain diode forward characteristics

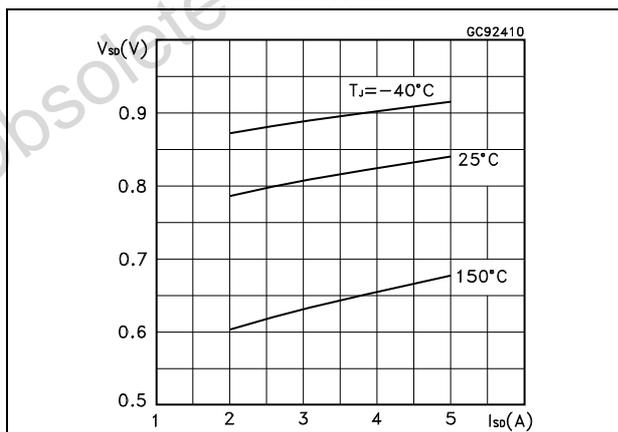


Figure 7. Static drain-source on resistance

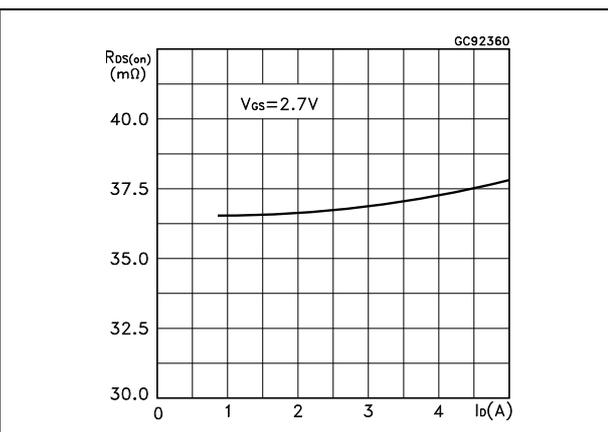


Figure 8. Gate charge vs gate-source voltage

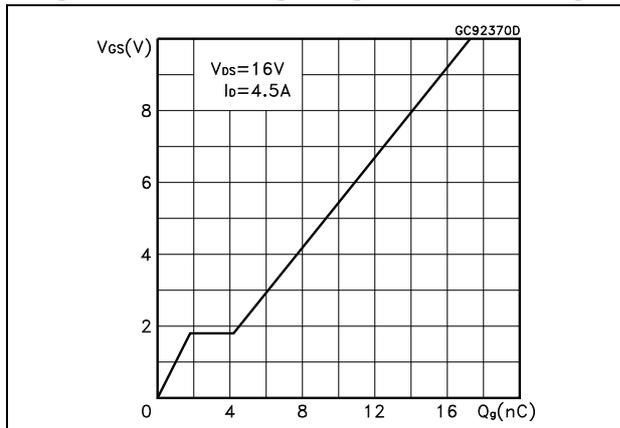


Figure 9. Capacitance variations

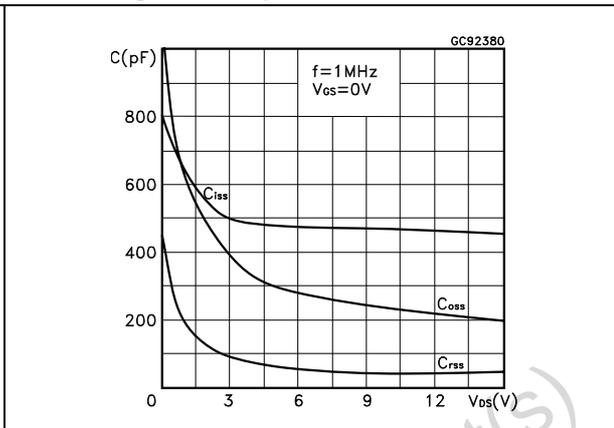


Figure 10. Normalized gate threshold voltage vs temperature

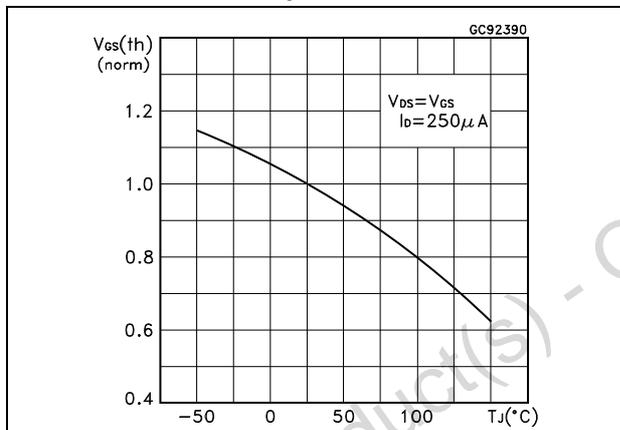
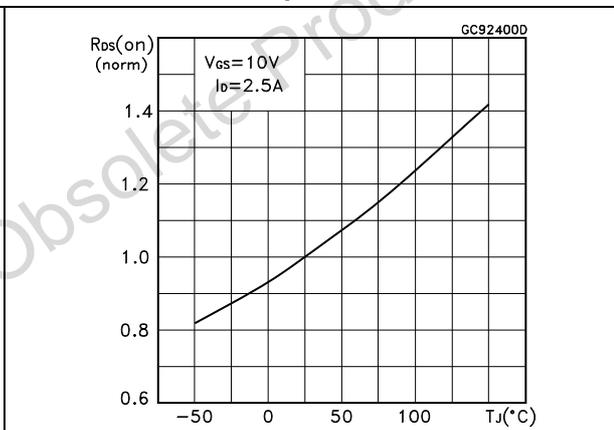
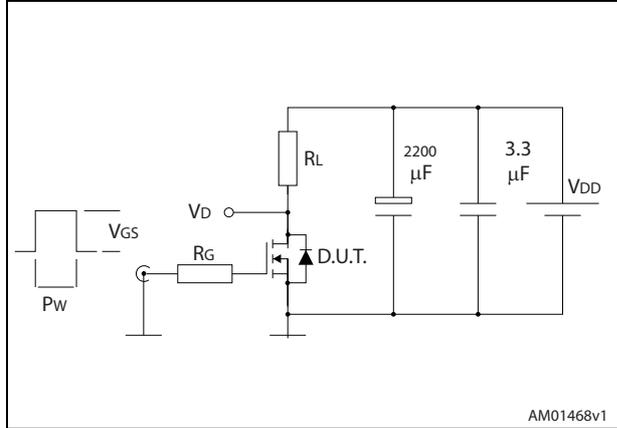


Figure 11. Normalized on-resistance vs temperature



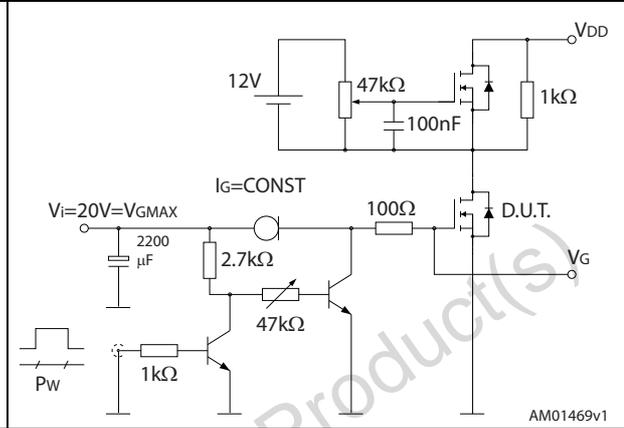
3 Test circuit

Figure 12. Switching times test circuit for resistive load



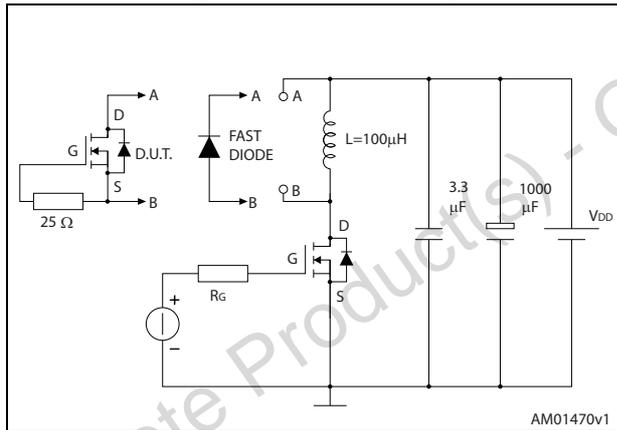
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Figure 13. Gate charge test circuit



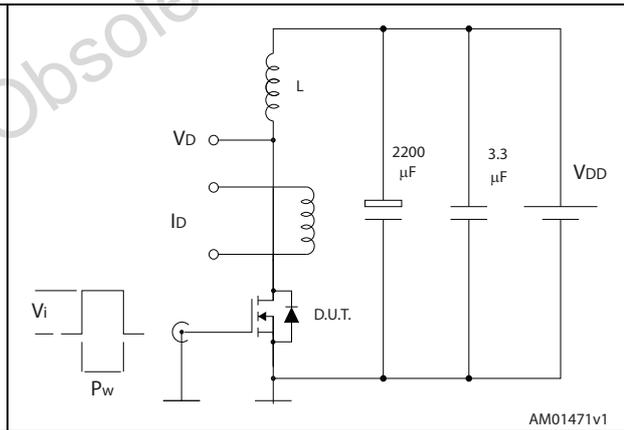
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Figure 14. Test circuit for inductive load switching and diode recovery times



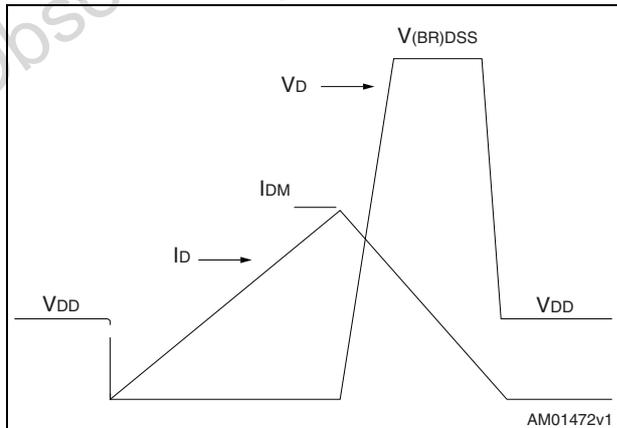
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Figure 15. Unclamped Inductive load test circuit



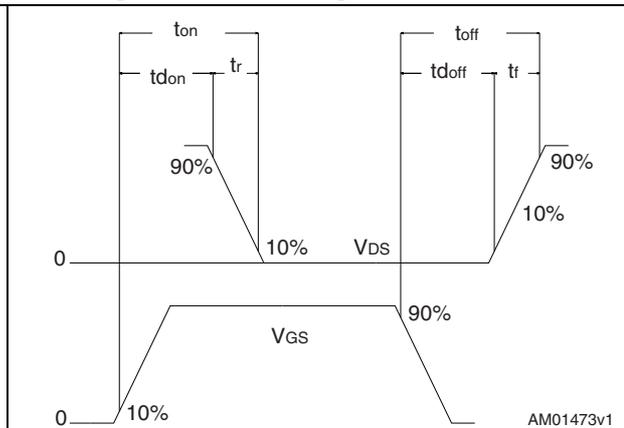
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Figure 16. Unclamped inductive waveform



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Figure 17. Switching time waveform



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4 Package mechanical data

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Figure 18. SO-8 drawing

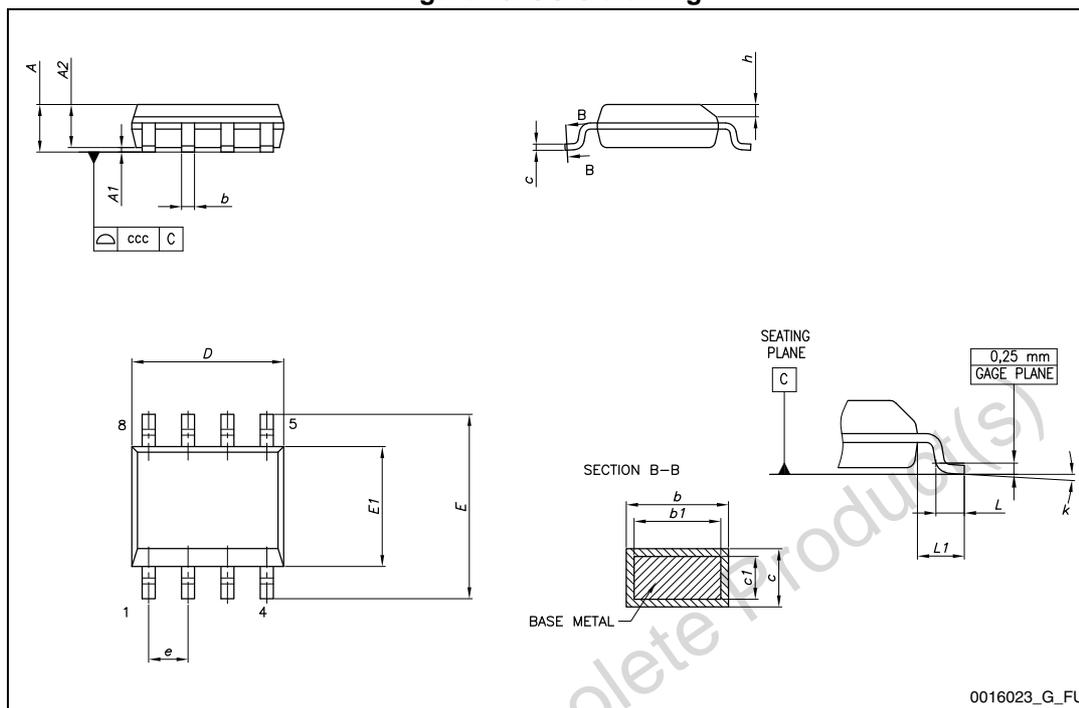
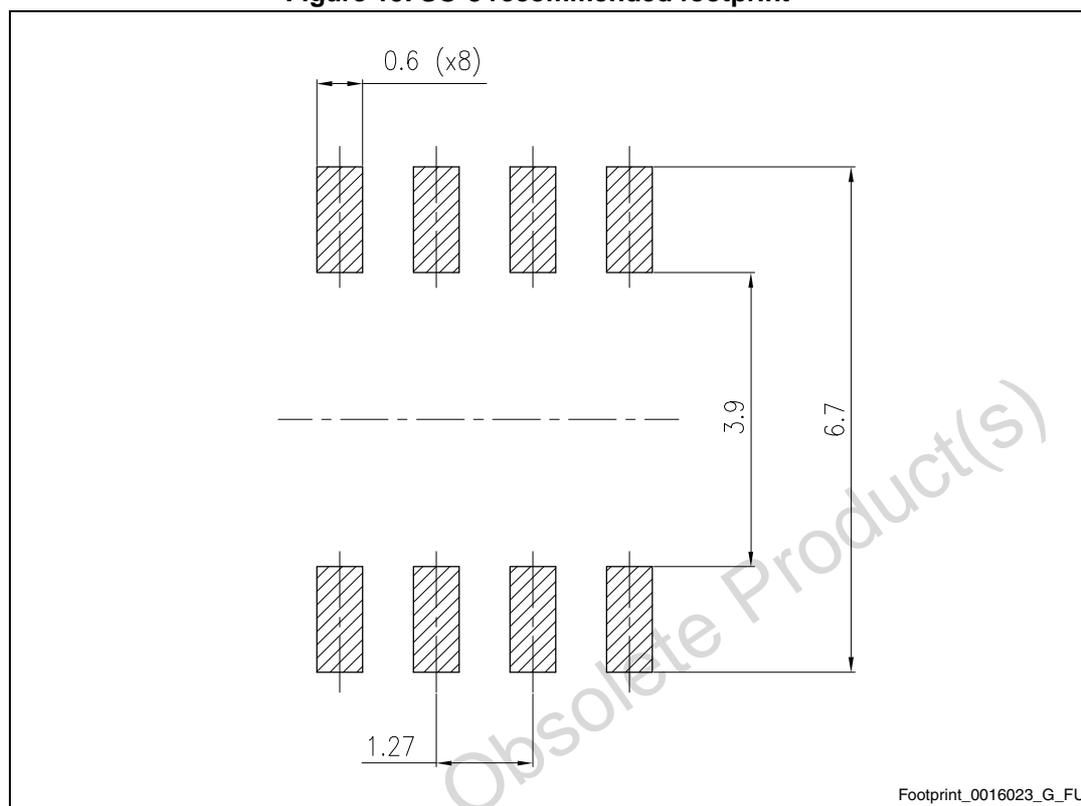


Table 8. SO-8 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.31		0.51
b1	0.28		0.48
c	0.10		0.25
c1	0.10		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
L2		0.25	
k	0°		8°
ccc			0.10

Figure 19. SO-8 recommended footprint^(a)



a. All dimensions are in millimeters.

5 Revision history

Table 9. Revision history

Date	Revision	Changes
21-Jun-2004	4	Complete document
13-Nov-2006	5	The document has been reformatted
02-May-2011	6	<i>Table 1: Device summary</i> has been corrected
06-Mar-2014	7	Modified: Marking in <i>Table 1</i> Updated: <i>Section 4: Package mechanical data, Figure 12: Switching times test circuit for resistive load, Figure 13: Gate charge test circuit, Figure 14: Test circuit for inductive load switching and diode recovery times</i> and <i>Figure 15: Unclamped Inductive load test circuit.</i> Minor text changes.

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